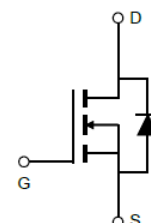
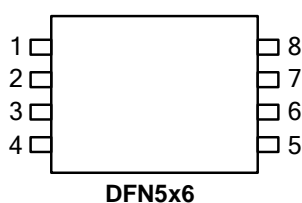


N-Channel Power MOSFET

<p>General Description</p> <ul style="list-style-type: none"> • Very low on-resistance $R_{DS(ON)}$ • Low Gate Charge • Excellent Gate Charge x $R_{DS(ON)}$ Product <p>Applications</p> <ul style="list-style-type: none"> • High Frequency Switching and Synchronous Rectification 	<p>Product Summary</p> <table border="0"> <tr> <td>V_{DS}</td> <td>40V</td> </tr> <tr> <td>I_D</td> <td>130A</td> </tr> <tr> <td>$R_{DS(ON)}$ (at $V_{GS}=10V$)</td> <td>< 1.7mΩ</td> </tr> <tr> <td>$R_{DS(ON)}$ (at $V_{GS}=4.5V$)</td> <td>< 2.4mΩ</td> </tr> </table> <p>100% DVDS Tested 100% UIS Tested 100% Rg Tested</p>	V_{DS}	40V	I_D	130A	$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 1.7m Ω	$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 2.4m Ω
V_{DS}	40V								
I_D	130A								
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 1.7m Ω								
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 2.4m Ω								



Part Number	Package Type	Form	Marking
SL130N04Q	DFN5x6	Tape & Reel	SL130N04Q

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	Silicon Limited	130
		$T_C = 100^\circ\text{C}$ ^B	100
Pulsed Drain Current ^A	I_{DM}	400	A
Avalanche Current ^A	I_{AS}	40	A
Single Pulse Avalanche Energy	E_{AS}	400	mJ
Power Dissipation ^C	P_D	$T_C = 25^\circ\text{C}$	125
		$T_C = 100^\circ\text{C}$	--
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Case	$R_{\theta JC}$	1	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient	$R_{\theta JA}$	50	

Electrical Characteristics($T_J = 25^\circ\text{C}$ unless otherwise noted)						
Symbol	Parameter	Conditions	Value			Units
			Min	Typ	Max	
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	40			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 45\text{V}, V_{GS} = 0\text{V}$	$T_J = 25^\circ\text{C}$		1	μA
			$T_J = 125^\circ\text{C}$		5	
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.2	1.6	2.4	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{V}, I_D = 30\text{A}$		1.5	1.7	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 30\text{A}$		2	2.4	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		53		S
V_{SD}	Diode Forward Voltage	$I_S = 30\text{A}, V_{GS} = 0\text{V}$			1.2	V
I_S	Maximum Body-Diode Continuous Current ^B				100	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		3972		pF
C_{oss}	Output Capacitance			1119		
C_{rss}	Reverse Transfer Capacitance			82		
R_g	Gate Resistance	$f = 1\text{MHz}$		1.0		Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS} = 10\text{V}, V_{DS} = 20\text{V}, I_D = 20\text{A}$		--		nC
$Q_g(4.5\text{V})$	Total Gate Charge			45		
Q_{gs}	Gate Source Charge			12		
Q_{gd}	Gate Drain Charge			18.5		
Q_{oss}	Output Charge	$V_{GS} = 0\text{V}, V_{DS} = 20\text{V}$		--		
$t_{D(on)}$	Turn-On Delay Time	$V_{GS} = 10\text{V}, V_{DS} = 20\text{V}, I_D = 20\text{A}, R_G = 1.6\Omega$		18.5		ns
t_r	Turn-On Rise Time			9		
$T_{D(off)}$	Turn-Off Delay Time			58.5		
t_f	Turn-Off Fall Time			32		
t_{rr}	Body Diode Reverse Recovery Time	$I_F = 20\text{A}, di/dt = 100\text{A}/\mu\text{s}$		--		ns
Q_{rr}	Body Diode Reverse Recovery Charge			--		nC

A. Single pulse width limited by maximum junction temperature.

B. The maximum current rating is package limited.

C. The power dissipation P_D is based on $T_{J(MAX)} = 150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

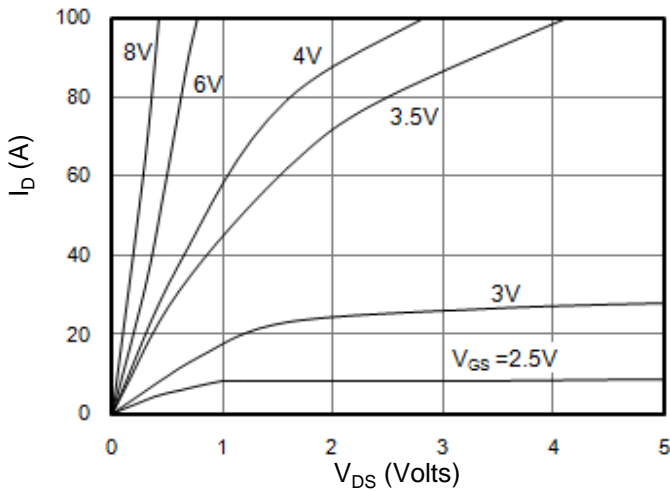


Figure 1: On-Region Characteristics

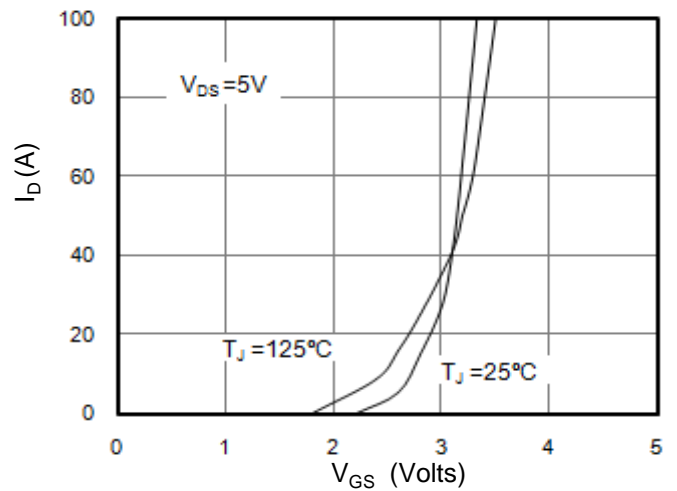


Figure 2: Transfer Characteristics

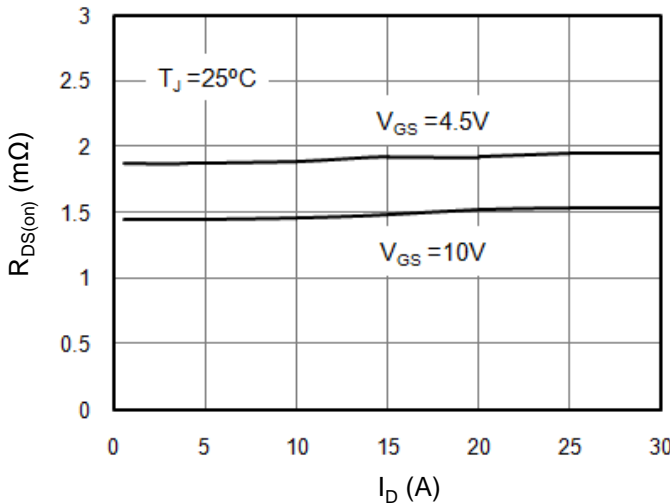


Figure 3: On-Resistance vs. Drain Current

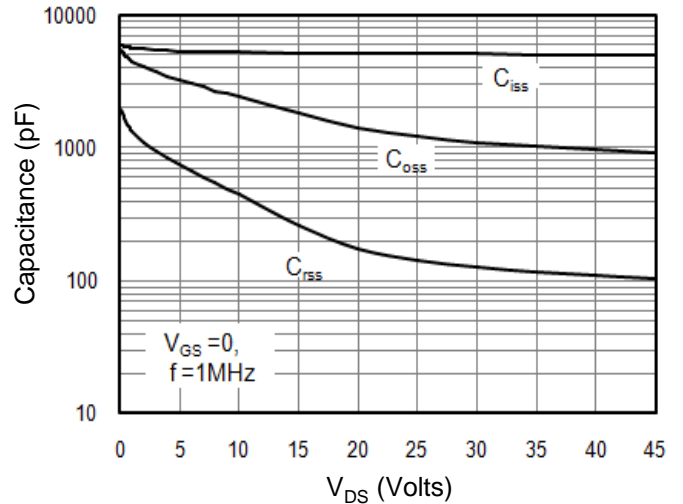


Figure 4: Capacitance Characteristics

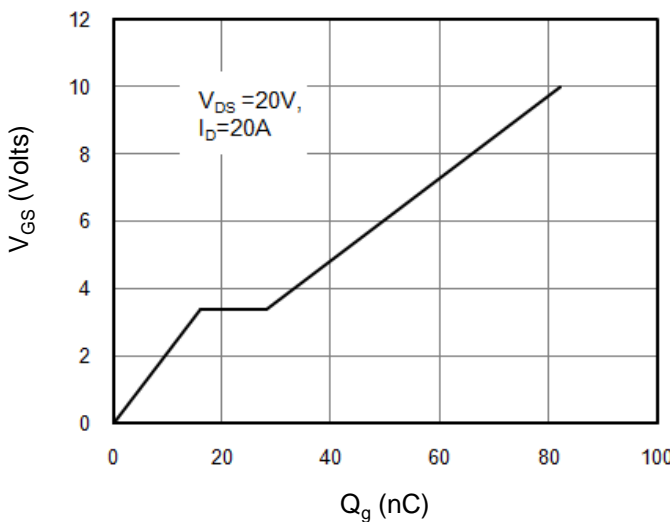


Figure 5: Gate Charge Characteristics

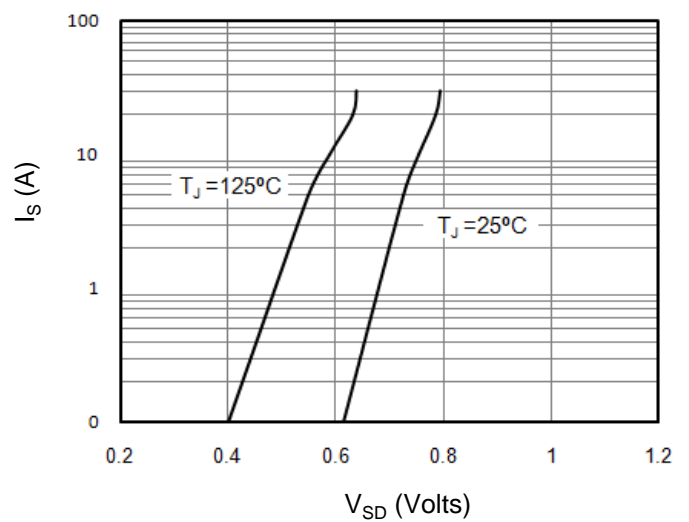


Figure 6: Body Diode Forward Voltage

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

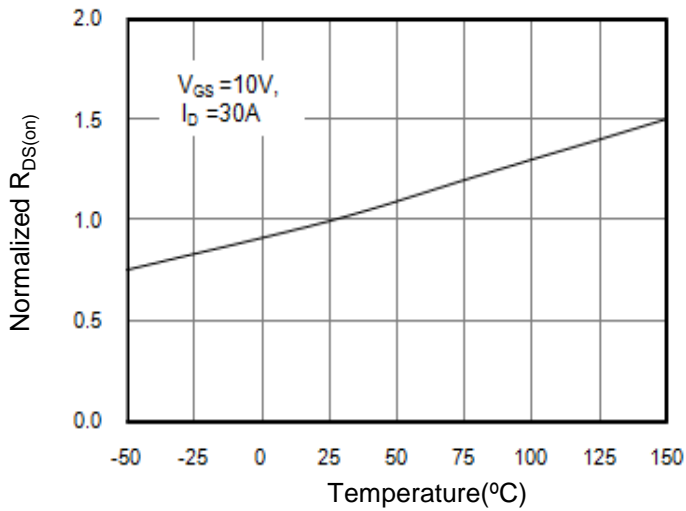


Figure 7: On-Resistance vs. Junction Temperature

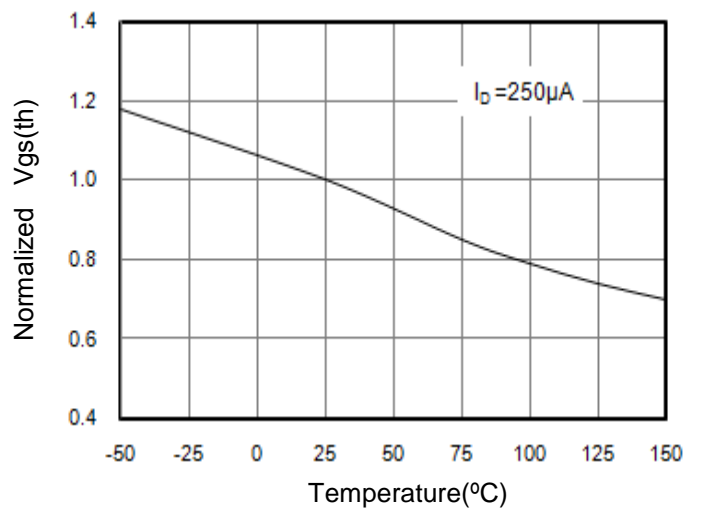


Figure 8: $V_{GS(th)}$ vs. Junction Temperature

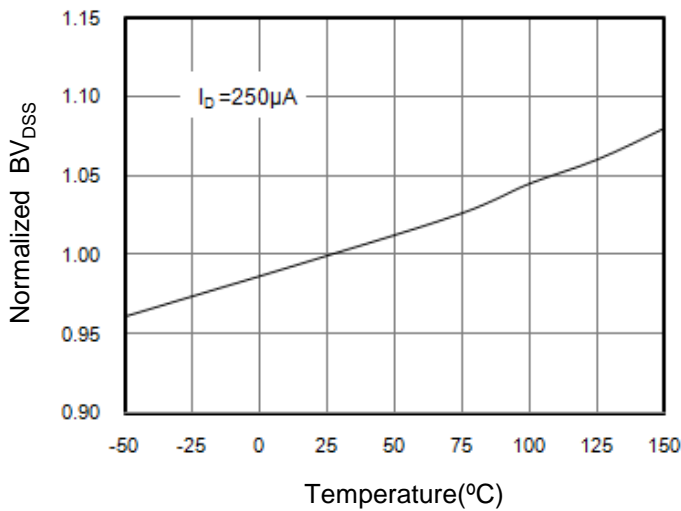


Figure 9: BV_{DS} vs. Junction Temperature

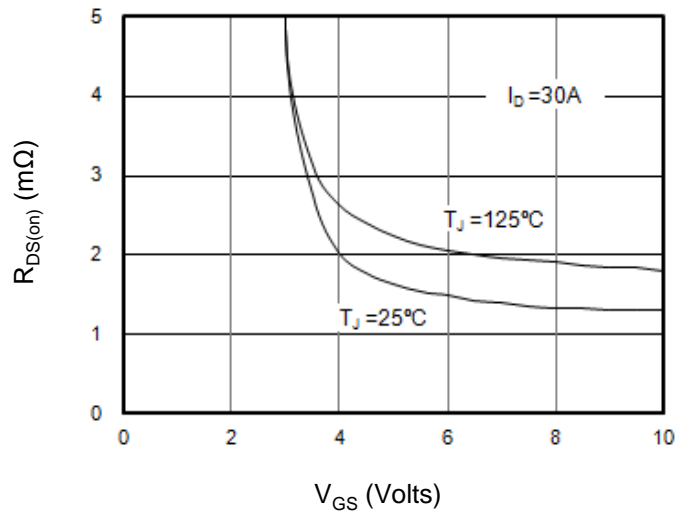


Figure 10: On-Resistance vs. Gate-Source Voltage

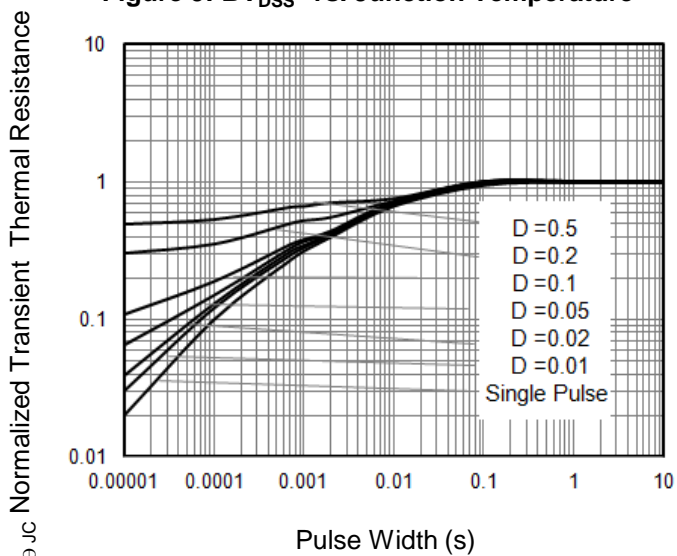


Figure 11: Normalized Transient Thermal Resistance

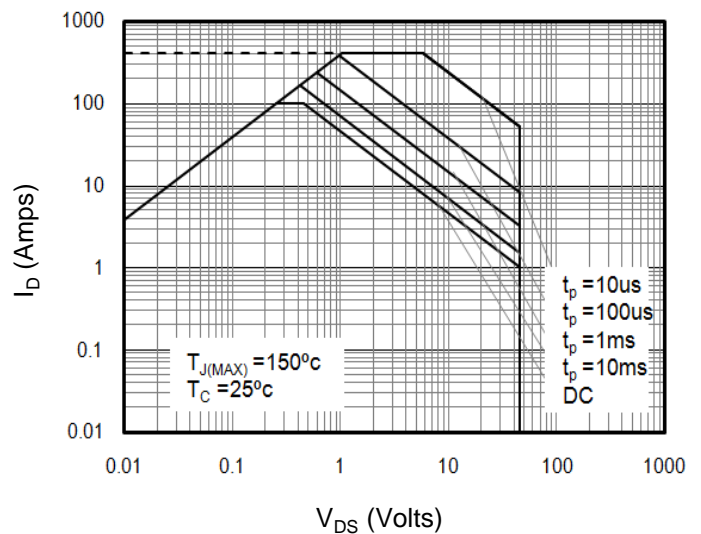
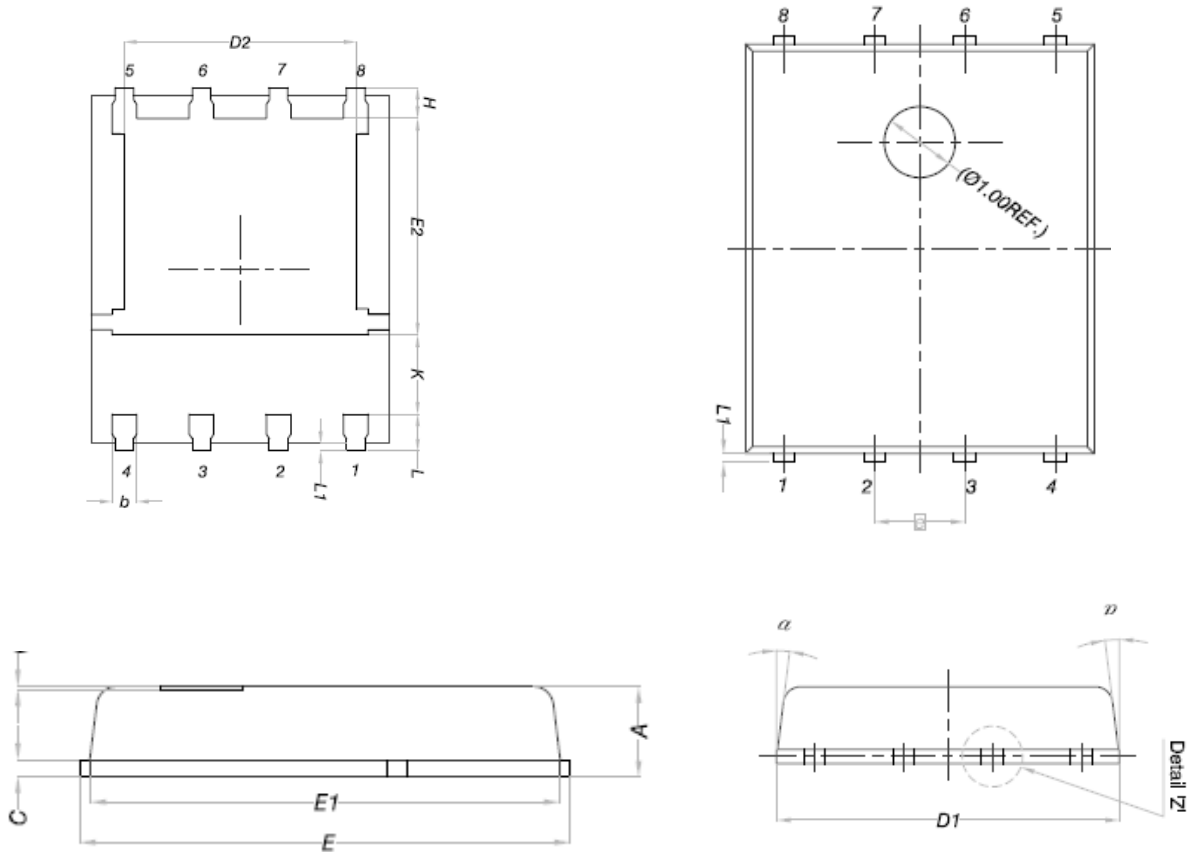


Figure 12: Safe Operating Area

DFN5x6


DIM.	MILLIMETERS			DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.		MIN.	NOM.	MAX.
A	0.90	1.00	1.10	E	5.90	6.00	6.10
A1	0	-	0.05	E1	5.70	5.75	5.80
b	0.33	0.41	0.51	E2	3.38	3.58	3.78
C	0.20	0.25	0.30	e	1.27 BSC		
D1	4.80	4.90	5.00	H	0.41	0.51	0.61
D2	3.61	3.81	3.96	K	1.10	-	-
				L	0.51	0.61	0.71
				L1	0.06	0.13	0.20
				alpha	0°	-	12°